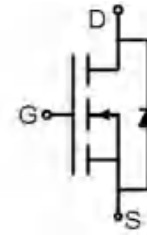


APG250N01

N-Channel Enhancement Mosfet

Feature

- 100V,40A
 $R_{DS(ON)} < 25m\Omega @ V_{GS}=10V$ (TYP:18m Ω)
 $R_{DS(ON)} < 38m\Omega @ V_{GS}=4.5V$ (TYP:25m Ω)
- Split Gate Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram

Application

- PWM applications
- Load Switch
- Power management



Marking and pin Assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
G250N01	APG250N01	TO-220	-	-	1000

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a=25^\circ\text{C}$)	I_D	40	A
Continuous Drain Current ($T_a=100^\circ\text{C}$)	I_D	25	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	160	A
Single Pulsed Avalanche Energy ⁽²⁾	E_{AS}	16	mJ
Power Dissipation	P_D	45	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

APG250N01

N-Channel Enhancement Mosfet

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$	-	-	1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage ⁽³⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.8	2.8	V
Drain-source on-resistance ⁽³⁾	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 15A$	-	18	25	$m\Omega$
		$V_{GS} = 4.5V, I_D = 10A$	-	25	38	$m\Omega$
Forward Threshold Voltage	g_{fs}	$V_{DS} = 10V, I_D = 20A$	-	22	-	S
Gate Resistance	R_g	$V_{DS} = V_{GS} = 0V, f = 1MHz$	-	1.62	-	Ω
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$	-	822	-	pF
Output Capacitance	C_{oss}		-	310	-	
Reverse Transfer Capacitance	C_{rss}		-	23.5	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50V, I_D = 20A,$ $V_{GS} = 10V, R_G = 3\Omega$	-	15	-	ns
Turn-on rise time	t_r		-	3.2	-	
Turn-off delay time	$t_{d(off)}$		-	30	-	
Turn-off fall time	t_f		-	7.6	-	
Total Gate Charge	Q_g	$V_{DS} = 50V, I_D = 20A,$ $V_{GS} = 10V$	-	22.7	-	nC
Gate-Source Charge	Q_{gs}		-	6.2	-	
Gate-Drain Charge	Q_{gd}		-	5.3	-	
Reverse Recovery Charge	Q_{rr}	$I_F = 20A, di/dt = 100A/\mu s$	-	59	-	nC
Reverse Recovery Time	T_{rr}	$I_F = 20A, di/dt = 100A/\mu s$	-	45	-	ns
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$V_{GS} = 0V, I_S = 10A$	-	-	1.2	V
Diode Forward current ⁽⁴⁾	I_S		-	-	40	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: $T_J = 25^\circ\text{C}, V_{DD} = 50V, R_G = 25\Omega, L = 0.5\text{Mh}$
3. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
4. Surface Mounted on FR4 Board, $t \leq 10$ sec

Typical Performance Characteristics

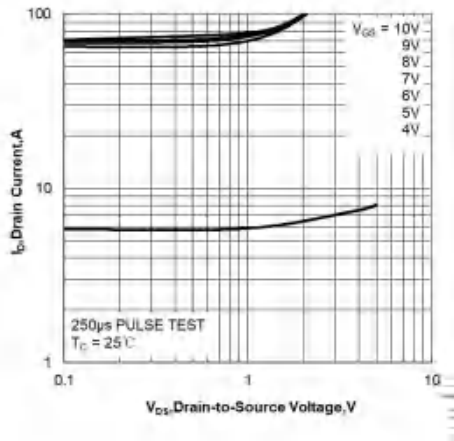


Figure 1. Output Characteristics

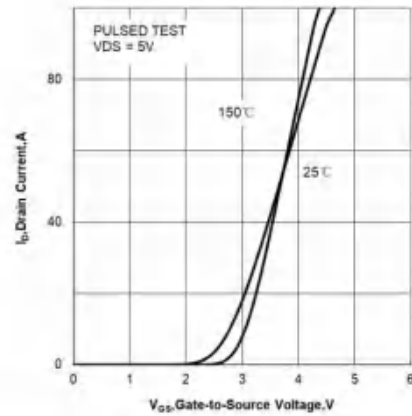


Figure 2. Transfer Characteristics

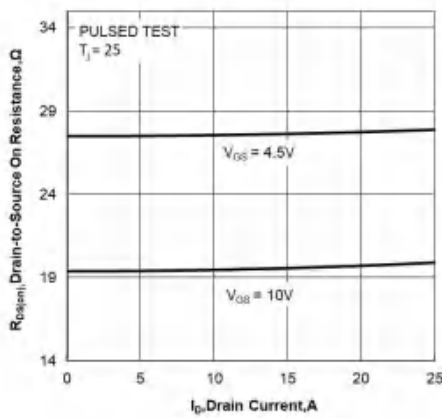


Figure 3. Drain-to-Source On Resistance vs Drain Current

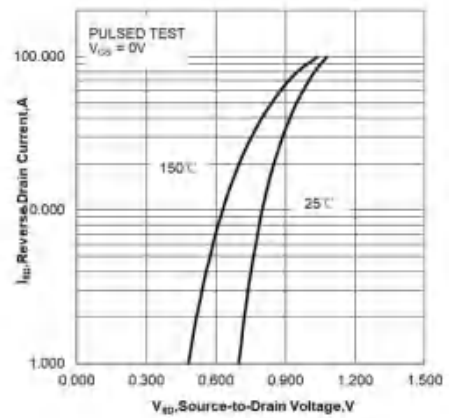


Figure 4. Body Diode Forward Voltage vs Source Current and Temperature

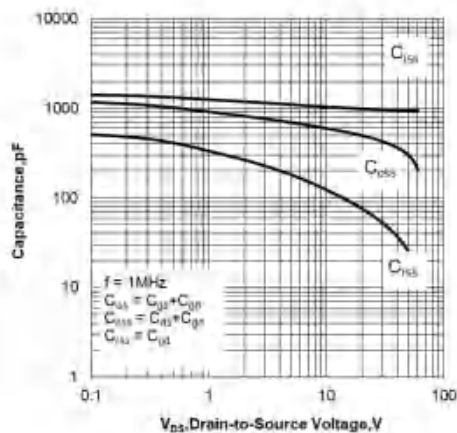


Figure 5. Capacitance Characteristics

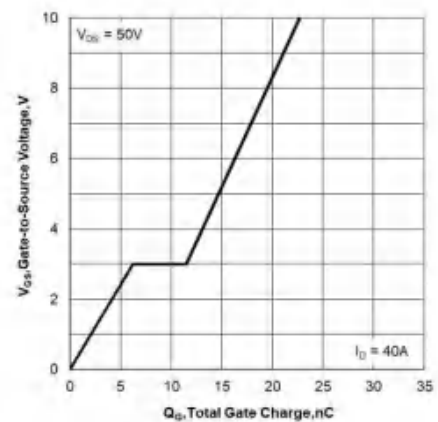


Figure 6. Gate Charge Characteristics

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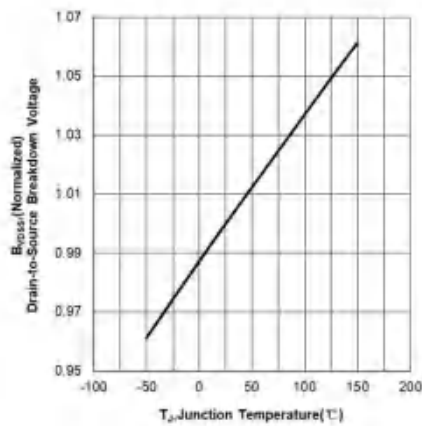


Figure 7. Normalized Breakdown Voltage vs Junction Temperature

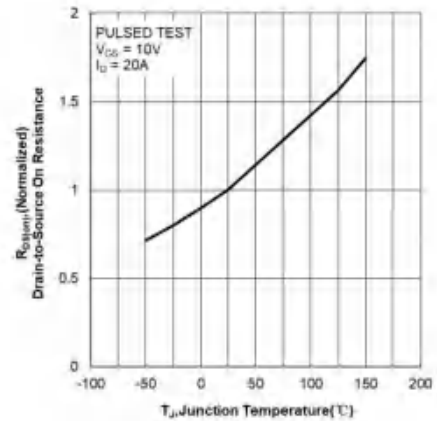


Figure 8. Normalized On Resistance vs Junction Temperature

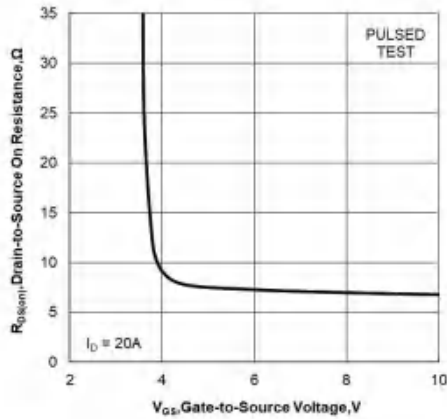


Figure 9. Drain-to-Source On Resistance vs Gate Voltage and Drain Current

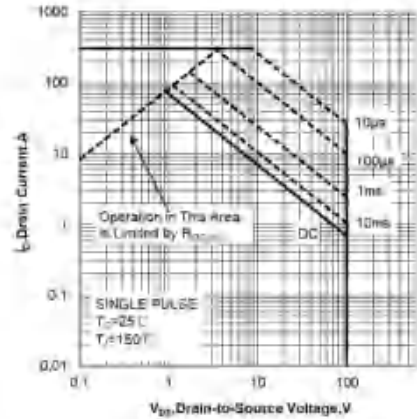


Figure 10. Maximum Safe Operating Area

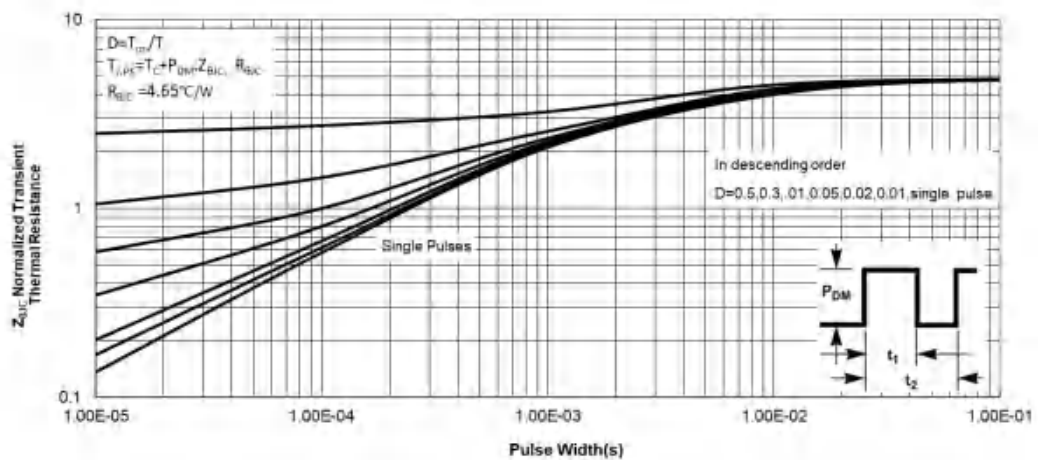
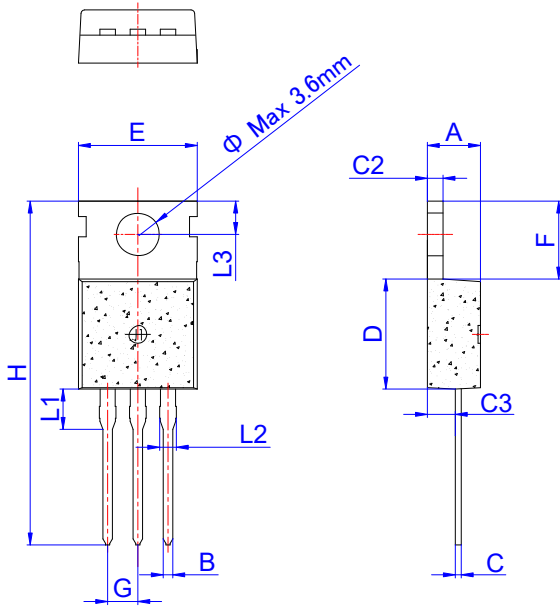


Figure 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

TO-220 Package Information



TO-220

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	